

Insulated Single Phase Hyperfast Bridge (Power Modules), 60 A



SOT-227

PRIMARY CHARACTERISTICS						
V _{RRM}	650 V					
I _O at T _C = 123 °C	60 A					
t _{rr}	63 ns					
Туре	Modules - Bridge, Hyperfast					
Package	SOT-227					
Circuit configuration	Single phase bridge					

FEATURES

- · Hyperfast and soft recovery characteristic
- · Electrically isolated base plate
- · Simplified mechanical designs, rapid assembly



- Designed and qualified for industrial and consumer level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

ABSOLUTE MAXIMUM RATINGS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
		60	Α				
Io	T _C	123	°C				
I _{FSM}	50 Hz	360	۸				
	60 Hz	377	Α				
121	50 Hz	648	A2-				
I ² t	60 Hz	589	A ² s				
V _{RRM}		650	V				
T _J		-55 to +175	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J MAXIMUM mA				
UFH60BA65	65	650	700	2				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	MBOL TEST CONDITIONS MIN. TYP. MAX				UNITS	
Cathode to anode breakdown voltage	V_{BR}	I _R = 250 μA	650	-	ı	V	
Forward voltage, per diode	V_{FM}	I _F = 60 A	-	1.7	2.35	V	
Reverse leakage current, per leg	1	V _R = 650 V	-	1.0	100		
heverse leakage current, per leg	I _{RM}	V _R = 650 V, T _J = 150 °C	-	250	-	μΑ	
RMS isolation voltage base plate	V _{ISOL}	f = 50 Hz, any terminal to case, t = 1 min	2500	-	-	V	



FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS V			VALUES	UNITS
Maximum DC output current	_	Resistive or inc	Resistive or inductive load			Α
at case temperature	I _O				123	°C
		t = 10 ms	No voltage		360	
Maximum peak, one-cycle		t = 8.3 ms	reapplied	Initial T _J = 25 °C	377	А
non-repetitive forward current	I _{FSM}	t = 10 ms	100 % V _{RRM}		303	
		t = 8.3 ms	reapplied		317	
	l ² t	t = 10 ms	No voltage		648	- A ² s
Maximum 12t fax fusing		t = 8.3 ms	reapplied		589	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		458	
		t = 8.3 ms	reapplied		417	
Maximum I ² √t for fusing	l²√t	I ² t for time t _x =	$I_2\sqrt{t} \times \sqrt{t_x}$; $0.1 \le t_x \le 1$	0 ms, V _{RRM} = 0 V	6.4	kA²√s
Low level of threshold voltage, per leg	V _{F(T0)1}	(4C 7.0/ ·· ··· · · · · · · · · · · · · · · ·		16.49	V	
Low level value of forward slope resistance	r _{f1}	(16.7 % x π x I _{F(AV)}) < I < π x I _{F(AV)} , T _J = T _J maximum 0.88				mΩ
High level of threshold voltage, per leg	V _{F(T0)2}	15.8			15.87	V
High level value of forward slope resistance	r _{f2}	$(1 > \pi \times 1_{E(A \setminus f)}), 1 = 1 \cup 1_{E(A \setminus f)}$				mΩ
Maximum forward voltage, per diode	V_{FM}	I _F = 60 A 2.35 V			V	

RECOVERY CHARACTERISTIC	S				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical reverse recovery time, per diode		$T_J = 25 ^{\circ}\text{C}$, $I_F = 50 \text{A}$, $V_R = 200 \text{V}$, $dI_F/dt = 200 \text{A}/\mu\text{s}$	63	ns	
Typical reverse recovery time, per diode	t _{rr}	$T_J = 125 ^{\circ}\text{C}, I_F = 50 \text{A}, V_R = 200 \text{V},$ $dI_F/dt = 200 \text{A}/\mu\text{s}$	134	115	· •
Tunical reverse receivers current per diade		$T_J = 25 ^{\circ}\text{C}$, $I_F = 50 \text{A}$, $V_R = 200 \text{V}$, $dI_F/dt = 200 \text{A}/\mu\text{s}$	4.1	А	I _{FM}
Typical reverse recovery current, per diode	I _{rr}	$T_J = 125$ °C, $I_F = 50$ A, $V_R = 200$ V, $dI_F/dt = 200$ A/ μ s	11.4	A	$\frac{dl_{R}}{dt}$ Q_{rr}
Typical reverse recovery charge, per diode	0	$T_J = 25 ^{\circ}\text{C}, \ I_F = 50 \text{A}, \ V_R = 200 \text{V}, \ dI_F/dt = 200 \text{A}/\mu\text{s}$	130	nC	I _{RM(REC)}
Typical reverse recovery charge, per diode	Q _{rr}	$T_J = 125 ^{\circ}\text{C}, \ I_F = 50 \text{A}, \ V_R = 200 \text{V}, \ dI_F/dt = 200 \text{A/}\mu\text{s}$	765		
Typical junction capacitance	C _T	V _R = 650 V	77	pF	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance junction to case	R _{thJC}		-	-	0.91	°C/W	
Thermal resistance case to heatsink	R _{thCS}	Flat, greased surface	-	0.1	-	C/VV	
Weight			-	30	-	g	
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf.in)	
Case style			SOT-227				

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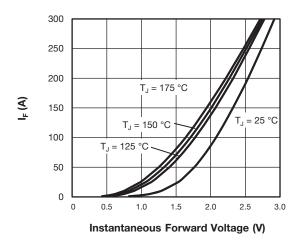


Fig. 1 - Typical Forward Voltage Characteristics

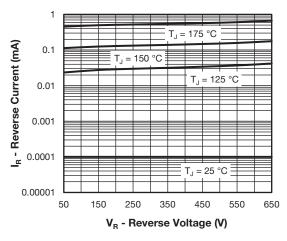


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

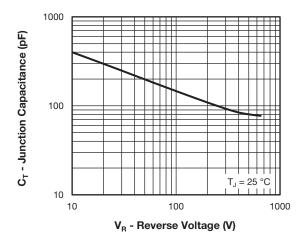


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Diode)

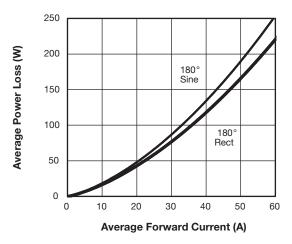


Fig. 4 - Forward Power Loss Characteristics

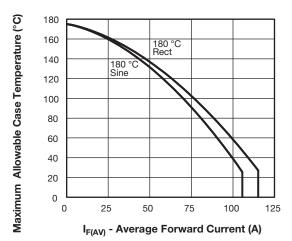


Fig. 5 - Current Rating Characteristics (A)

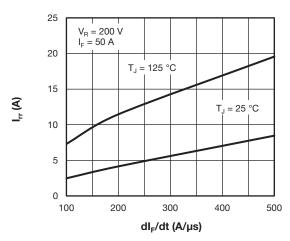
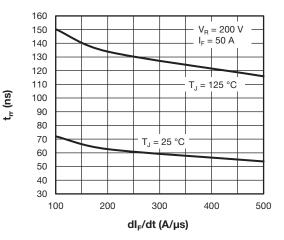


Fig. 6 - Typical Reverse Recovery Current vs. dl_F/dt







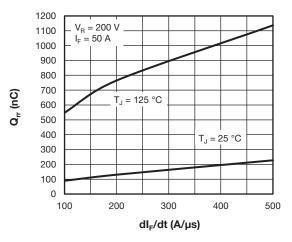


Fig. 8 - Reverse Recovery Charge vs. dl_F/dt

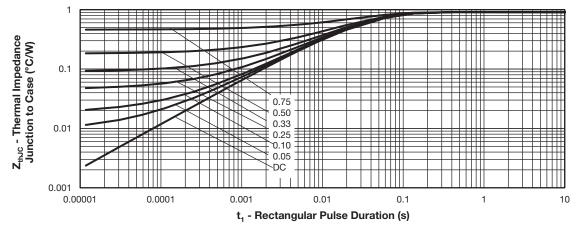
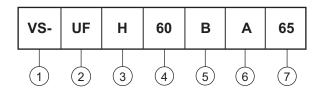


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt (Per Diode)



ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Ultra fast rectifier
- 3 Hyper fast FRED Pt® diffused
- Current rating (60 = 60 A)
- 5 Circuit configuration:
 - B = Single phase bridge
- 6 Package indicator:
 - A = SOT-227, standard insulated base
- 7 Voltage rating (65 = 650 V)

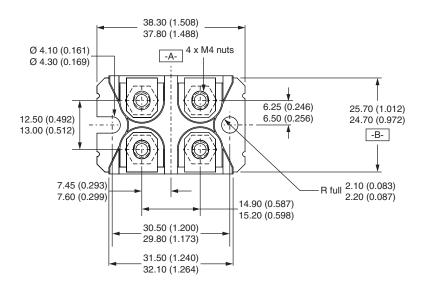
CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Single phase bridge	В	Lead Assignment (AC) 4 0 4 0 2 (AC) 1 2 2				

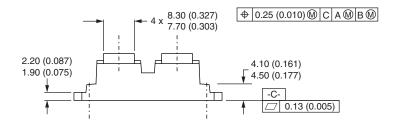
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				

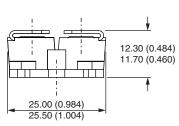


SOT-227 Generation II

DIMENSIONS in millimeters (inches)







Note

Controlling dimension: millimeter



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